Small Signal MOSFET

30 V, 154 mA, Single, N-Channel, Gate ESD Protection, SC-75

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- Pb-Free Package is Available

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players,
 Digital Cameras, PDA's, Video Games, Hand-Held Computers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Paramo	Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	30	V
Gate-to-Source Voltage		V _{GS}	±10	V
Continuous Drain Current (Note 1)	Steady State = 25°C	Ι _D	154	mA
Power Dissipation (Note 1)	Steady State = 25°C	P _D	300	mW
Pulsed Drain Current $t_P \le 10 \mu s$		I _{DM}	618	mA
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 150	°C
Continuous Source Current (Body Diode)		I _{SD}	154	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

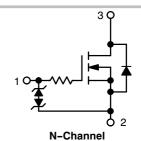
1. Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).



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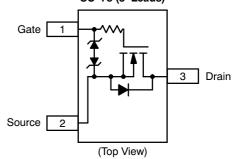
http://onsemi.com

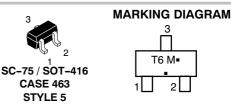
V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)
20.1/	1.4 Ω @ 4.5 V	154 m A
30 V	2.3 Ω @ 2.5 V	154 mA



PIN CONNECTIONS

SC-75 (3-Leads)





T6 = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTA7002NT1	SC-75	3000 Tape & Reel
NTA7002NT1G	SC-75 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

型语 CTRICATO CHARGE RISE CS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 30 V			1.0	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, $ $T = 85 ^{\circ}\text{C}$			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 10 \text{ V}$			±25	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 5 \text{ V}$			±1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 \text{ V, } V_{GS} = \pm 5 \text{ V}$ T = 85 °C			±1.0	μΑ
ON CHARACTERISTICS (Note 2)	<u>.</u>					
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = V_{GS}, I_{D} = 100 \mu A$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 154 \text{ mA}$		1.4	7.0	Ω
		V _{GS} = 2.5 V, I _D = 154 mA		2.3	7.5	
Forward Transconductance	g _{FS}	V _{DS} = 3 V, I _D = 154 mA		80		mS
CAPACITANCES						
Input Capacitance	C _{ISS}			11.5	20	
Output Capacitance	C _{OSS}	$V_{DS} = 5.0 \text{ V, f} = 1 \text{ MHz,} $ $V_{GS} = 0 \text{ V}$		10	15	pF
Reverse Transfer Capacitance	C _{RSS}	400		3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)						
Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 5.0 V,		13		ns
Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(OFF)}	$V_{GS} = 4.5 \text{ V}, V_{DS} = 5.0 \text{ V},$ $I_D = 75 \text{ mA}, R_G = 10 \Omega$		98		ns
Fall Time	t _f			60		
DRAIN-SOURCE DIODE CHARACTERISTICS	<u>.</u>					
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 154 \text{ mA}$		0.77	0.9	V

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES

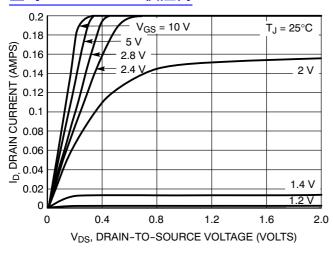
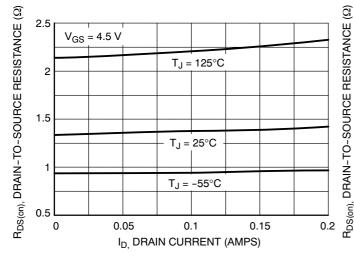


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



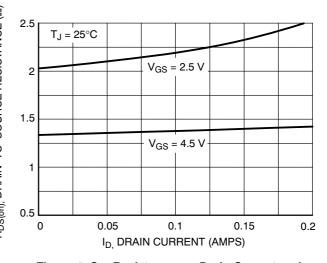
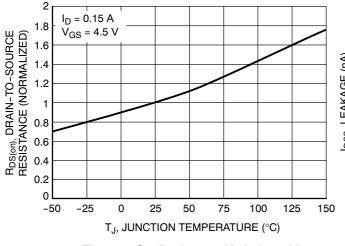


Figure 3. On-Resistance vs. Drain Current and Temperature

Figure 4. On-Resistance vs. Drain Current and Gate Voltage



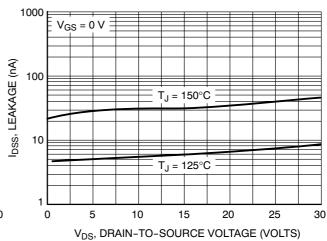
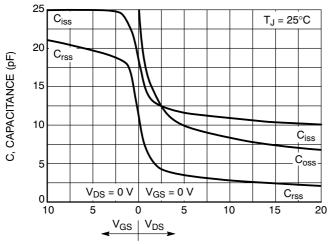


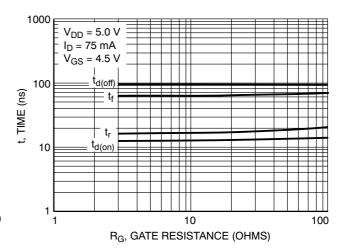
Figure 5. On-Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current vs. Voltage

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TYPICAL PERFORMANCE CURVES





GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (VOLTS)

Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation vs. Gate Resistance

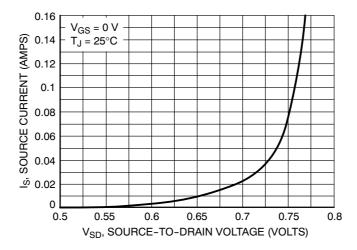
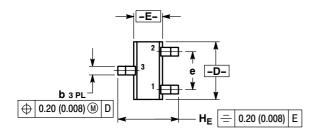


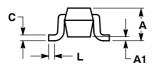
Figure 9. Diode Forward Voltage vs. Current

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PACKAGE DIMENSIONS

SC-75 / SOT-416 CASE 463-01 ISSUE F





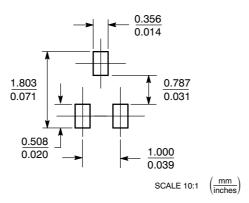
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14 5M 1982
- 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.70	0.80	0.90	0.027	0.031	0.035
A1	0.00	0.05	0.10	0.000	0.002	0.004
b	0.15	0.20	0.30	0.006	0.008	0.012
С	0.10	0.15	0.25	0.004	0.006	0.010
D	1.55	1.60	1.65	0.059	0.063	0.067
E	0.70	0.80	0.90	0.027	0.031	0.035
е	1.00 BSC		0	.04 BS0		
L	0.10	0.15	0.20	0.004	0.006	0.008
HE	1.50	1.60	1.70	0.061	0.063	0.065

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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